

TECHNICAL DATA DATA SHEET 4533, REV. A

HERMETIC SCHOTTKY RECTIFIER Low Forward Voltage Drop

Features:

- Soft Reverse Recovery at Low and High Temperature
- Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics

Maximum Ratings

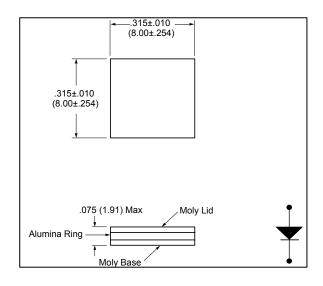
Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	200	V
Max. Average Forward Current	$I_{F(AV)}$	50% duty cycle, rectangular wave form (Single)	15	Α
Max. Average Forward Current	$I_{F(AV)}$	50% duty cycle, rectangular wave form (Common Cathode)	30	Α
Max. Peak One Cycle Non- Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine wave (per leg)	280	Α
Non-Repetitive Avalanche Energy	E _{AS}	$T_J = 25 ^{\circ}\text{C}, I_{AS} = 3.0 \text{A},$ L = 4.4 mH (per leg)	20	mJ
Repetitive Avalanche Current	I _{AR}	I_{AS} decay linearly to 0 in 1 μ s f limited by T_J max V_A =1.5 V_R	3.0	Α
Maximum Thermal Resistance	$R_{ heta JC}$	DC operation	0.85	°C/W
Max. Junction Temperature	TJ	-	-65 to +200	°C
Max. Storage Temperature	T_{stg}	-	-65 to +200	°C

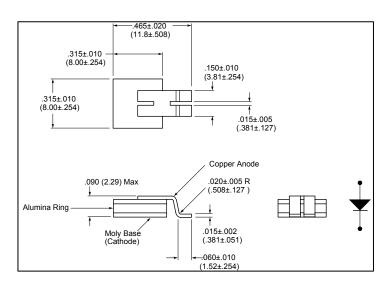
Electrical Characteristics

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V_{F1}	@ 15A, Pulse, T _J = 25 °C	0.92	\ \
(per leg)	V_{F2}	@ 15A, Pulse, T _J = 125 °C	0.76	V
Max. Reverse Current	I _{R1}	@V _R = 200V, Pulse,	0.015	mA
		T _J = 25 °C		
(per leg)	I _{R2}	@V _R = 200V, Pulse,	1.0	mA
		T _J = 125 °C		
Max. Junction Capacitance	C _T	$@V_R = 5V, T_C = 25 °C$	300	pF
(per leg)		$f_{SIG} = 1MHz,$		
		$V_{SIG} = 50 \text{mV (p-p)}$		

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MECHANICAL DIMENSIONS: In Inches / mm





SHD-2B

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Note: The V_f curves shown are for the SD125SCU200 unpackaged die only.

